Winbond Electronics Corp.

32K × 8 ELECTRICALLY ERASABLE EPROM

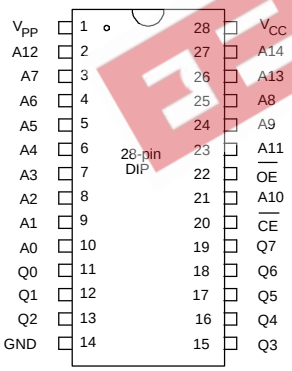
GENERAL DESCRIPTION

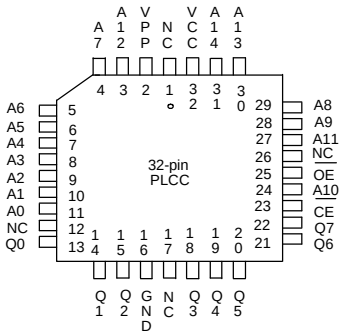
The W27E257 is a high-speed, low-power Electrically Erasable and Programmable Read Only Memory organized as 32768 × 8 bits that operates on a single 5 volt power supply. The W27E257 provides an electrical chip erase function. This part was the same EPROM Writer's utilities as the W27E256.

FEATURES

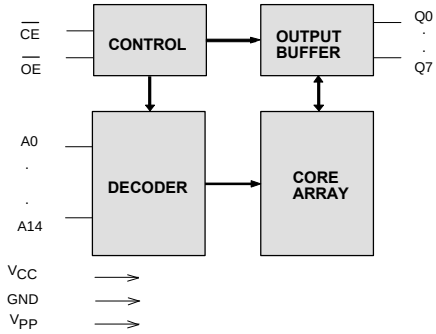
- High speed access time: 100/120/150 nS (max.)
- Read operating current: 15 mA (typ.)
- Erase/Programming operating current 1 mA (typ.)
- Standby current: 5 µA (typ.)
- Single 5V power supply
- +14V erase/+12V programming voltage
- Fully static operation
- All inputs and outputs directly TTL/CMOS compatible
- Three-state outputs
- Available packages: 28-pin 600 mil DIP and 32-pin PLCC

PIN CONFIGURATIONS





BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0–A14	Address Inputs
Q0–Q7	Data Inputs/Outputs
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
VPP	Program/Erase Supply Voltage
VCC	Power Supply
GND	Ground
NC	No Connection

FUNCTIONAL DESCRIPTION

Read Mode

Like conventional UVEPROMs, the W27E257 has two control functions, both of which produce data at the outputs.

$\overline{CE}$ is for power control and chip select. $\overline{OE}$ controls the output buffer to gate data to the output pins. When addresses are stable, the address access time (T_{ACC}) is equal to the delay from $\overline{CE}$ to output (T_{CE}), and data are available at the outputs T_{OE} after the falling edge of $\overline{OE}$, if T_{ACC} and T_{CE} timings are met.

Erase Mode

The erase operation is the only way to change data from "0" to "1." Unlike conventional UVEPROMs, which use ultraviolet light to erase the contents of the entire chip (a procedure that requires up to half an hour), the W27E257 uses electrical erasure. Generally, the chip can be erased within 100 mS by using an EPROM writer with a special erase algorithm.

Erase mode is entered when V_{PP} is raised to V_{PE} (14V), V_{CC} = V_{CE} (5V), $\overline{OE}$ = V_{IH} (2V or above but lower than V_{CC}), A9 = V_{HH} (14V), A0 = V_{IL} (0.8V or below but higher than GND), and all other address pins equal V_{IL} and data input pins equal V_{IH}. Pulsing $\overline{CE}$ low starts the erase operation.

Erase Verify Mode

After an erase operation, all of the bytes in the chip must be verified to check whether they have been successfully erased to "1" or not. The erase verify mode automatically ensures a substantial erase margin. This mode will be entered after the erase operation if V_{PP} = V_{PE} (14V), $\overline{CE}$ = V_{IH}, and $\overline{OE}$ = V_{IL}.

Program Mode

Programming is performed exactly as it is in conventional UVEPROMs, and programming is the only way to change cell data from "1" to "0." The program mode is entered when V_{PP} is raised to V_{PP} (12V), V_{CC} = V_{CP} (5V), $\overline{OE}$ = V_{IH}, the address pins equal the desired address, and the input pins equal the desired inputs. Pulsing $\overline{CE}$ low starts the programming operation.

Program Verify Mode

All of the bytes in the chip must be verified to check whether or not they have been successfully programmed with the desired data. Hence, after each byte is programmed, a program verify operation should be performed. The program verify mode automatically ensures a substantial program margin. This mode will be entered after the program operation if V_{PP} = V_{PP} (12V), $\overline{CE}$ = V_{IH}, and $\overline{OE}$ = V_{IL}.

Erase/Program Inhibit

Erase or program inhibit mode allows parallel erasing or programming of multiple chips with different data. When $\overline{CE}$ = V_{IH}, erasing or programming of non-target chips is inhibited, so that except for the $\overline{CE}$ and $\overline{OE}$ pins, the W27E257 may have common inputs.

Standby Mode

The standby mode significantly reduces V_{CC} current. This mode is entered when $\overline{CE}$ = V_{IH}. In standby mode, all outputs are in a high impedance state, independent of $\overline{OE}$.

Two-line Output Control

Since EPROMs are often used in large memory arrays, the W27E257 provides two control inputs for multiple memory connections. Two-line control provides for lowest possible memory power dissipation and ensures that data bus contention will not occur.

System Considerations

EPROM power switching characteristics require careful device decoupling. System designers are interested in three supply current issues: standby current levels (I_{SB}), active current levels (I_{CC}), and transient current peaks produced by the falling and rising edges of $\overline{CE}$. Transient current magnitudes depend on the device output's capacitive and inductive loading. Two-line control and proper decoupling capacitor selection will suppress transient voltage peaks. Each device should have a 0.1 µF ceramic capacitor connected between its V_{CC} and GND. This high frequency, low inherent-inductance capacitor should be placed as close as possible to the device. Additionally, for every eight devices, a 4.7 µF electrolytic capacitor should be placed at the array's power supply connection between V_{CC} and GND. The bulk capacitor will overcome voltage slumps caused by PC board trace inductances.

TABLE OF OPERATING MODES

(V_{PP} = 12V, V_{PE} = 14V, V_{HH} = 12V, V_{CP} = 5V, X = V_{IH} or V_{IL})

MODE	PINS						
	$\overline{CE}$	$\overline{OE}$	A0	A9	V_{CC}	V_{PP}	OUTPUTS
Read	V_{IL}	V_{IL}	X	X	V_{CC}	V_{CC}	D_{OUT}
Output Disable	V_{IL}	V_{IH}	X	X	V_{CC}	V_{CC}	High Z
Standby (TTL)	V_{IH}	X	X	X	V_{CC}	V_{CC}	High Z
Standby (CMOS)	V_{CC} ±0.3V	X	X	X	V_{CC}	V_{CC}	High Z
Program	V_{IL}	V_{IH}	X	X	V_{CP}	V_{PP}	D_{IN}
Program Verify	V_{IH}	V_{IL}	X	X	V_{CP}	V_{PP}	D_{OUT}
Program Inhibit	V_{IH}	V_{IH}	X	X	V_{CP}	V_{PP}	High Z
Erase	V_{IL}	V_{IH}	V_{IL}	V_{PE}	V_{CC}	V_{PE}	D_{IH}
Erase Verify	V_{IH}	V_{IL}	X	X	V_{CC}	V_{PE}	D_{OUT}
Erase Inhibit	V_{IH}	V_{IH}	X	X	V_{CP}	V_{PP}	High Z
Product Identifier-manufacturer	V_{IL}	V_{IL}	V_{IL}	V_{HH}	V_{CC}	V_{CC}	DA (Hex)
Product Identifier-device	V_{IL}	V_{IL}	V_{IH}	V_{HH}	V_{CC}	V_{CC}	02 (Hex)

DC CHARACTERISTICS

Absolute Maximum Ratings

PARAMETER	RATING	UNIT
Ambient Temperature with Power Applied	-55 to +125	°C
Storage Temperature	-65 to +125	°C
Voltage on all pins with Respect to Ground Except V_{PP}, A9 and V_{CC} pins	-0.5 to V_{CC} +0.5	V
Voltage on V_{PP} Pin with Respect to Ground	-0.5 to +14.5	V
Voltage on A9 Pin with Respect to Ground	-0.5 to +14.5	V
Voltage on V_{CC} Pin with Respect to Ground	-0.5 to +7	V

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

DC Erase Characteristics

(T_A = 25° C ±5° C, V_{CC} = 5.0V ±10%)

PARAMETER	SYM.	CONDITIONS	LIMITS			UNIT
			MIN.	TYP.	MAX.	
Input Load Current	I_{LI}	V_{IN} = V_{IL} or V_{IH}	-10	-	10	µA
V_{CC} Erase Current	I_{CP}	$\overline{CE}$ = V_{IL}	-	-	30	mA
V_{PP} Erase Current	I_{PP}	$\overline{CE}$ = V_{IL}	-	-	30	mA
Input Low Voltage	V_{IL}	-	-0.3	-	0.8	V
Input High Voltage	V_{IH}	-	2.4	-	5.5	V
Output Low Voltage (Verify)	V_{OL}	I_{OL} = 2.1 mA	-	-	0.45	V
Output High Voltage (Verify)	V_{OH}	I_{OH} = -0.4 mA	2.4	-	-	-
A9 Erase Voltage	V_{ID}	-	13.75	14	14.25	V
V_{PP} Erase Voltage	V_{PE}	-	13.75	14	14.25	V
V_{CC} Supply Voltage (Erase)	V_{CE}	-	4.5	5.0	5.5	V

Note: V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.

CAPACITANCE

(V_{CC} = 5V, T_A = 25° C, f = 1 MHz)

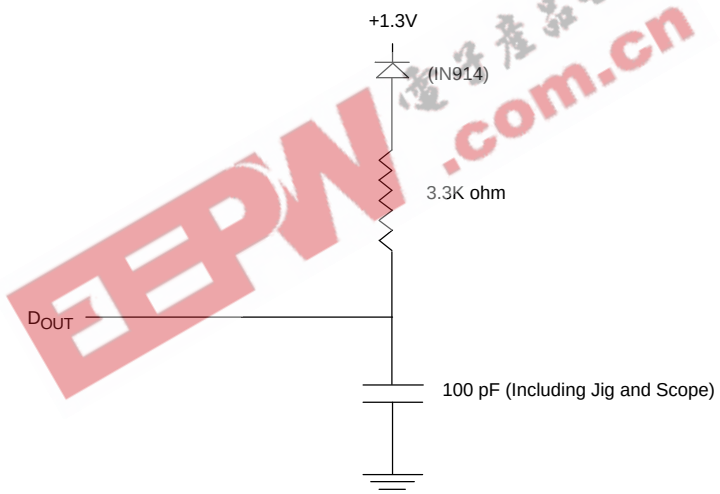
PARAMETER	SYMBOL	CONDITIONS	MAX.	UNIT
Input Capacitance	C_{IN}	V_{IN} = 0V	6	pF
Output Capacitance	C_{OUT}	V_{OUT} = 0V	12	pF

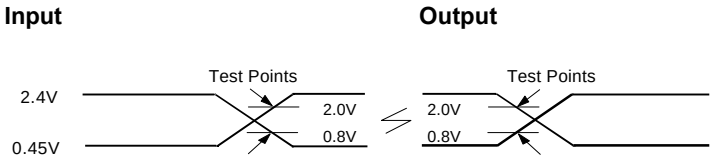
AC CHARACTERISTICS

AC Test Conditions

PARAMETER	CONDITIONS
Input Pulse Levels	0.45V to 2.4V
Input Rise and Fall Times	10 nS
Input and Output Timing Reference Level	0.8V/2.0V
Output Load	C_L = 100 pF, I_{OH}/I_{OL} = -0.4 mA/2.1 mA

AC Test Load and Waveform





READ OPERATION DC CHARACTERISTICS

(V_{CC} = 5.0V ±10%, T_A = 0 to 70° C)

(V_{CC}, min. = 3.0V and max. = 5.5V)

PARAMETER	SYM.	CONDITIONS	LIMITS			UNIT
			MIN.	TYP.	MAX.	
Input Load Current	I_{LI}	V_{IN} = 0V to V_{CC}	-5	-	5	µA
Output Leakage Current	I_{LO}	V_{OUT} = 0V to V_{CC}	-10	-	10	µA
V_{CC} Standby Current	I_{SB}	$\overline{CE}$ = V_{IH}	-	-	1.0	mA
	I_{SB1}	$\overline{CE}$ = V_{CC} ±0.2V	-	5	100	µA
V_{CC} Operating Current	I_{CC}	$\overline{CE}$ = V_{IL} I_{OUT} = 0 mA f = 5 MHz	-	-	30	mA
V_{PP} Operating Current	I_{PP}	V_{PP} = V_{CC}	-	-	100	µA
Input Low Voltage	V_{IL}	-	-0.3	-	0.8	V
Input High Voltage	V_{IH}	-	2.0	-	V_{CC} +0.5	V
Output Low Voltage	V_{OL}	I_{OL} = 2.1 mA	-	-	0.45	V
Output High Voltage	V_{OH}	I_{OH} = -0.4 mA	2.4	-	-	V
V_{PP} Operating Voltage	V_{PP}	-	V_{CC} -0.7	-	V_{CC}	V

READ OPERATION AC CHARACTERISTICS

(V_{CC} = 5.0V ±10%, T_A = 0 to 70° C)

PARAMETER	SYM.	W27E257-10		W27E257-12		W27E257-15		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	T_{RC}	100	-	120	-	150	-	nS
Chip Enable Access Time	T_{CE}	-	100	-	120	-	150	nS
Address Access Time	T_{ACC}	-	100	-	120	-	150	nS
Output Enable Access Time	T_{OE}	-	50	-	60	-	70	nS
$\overline{OE}$ High to High-Z Output	T_{DF}	-	30	-	30	-	50	nS
Output Hold from Address Change	T_{OH}	0	-	0	-	0	-	nS

Note: V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.

DC PROGRAMMING CHARACTERISTICS

(V_{CC} = 5.0V ±10%, T_A = 25° C ±5° C)

PARAMETER	SYM.	CONDITIONS	LIMITS			UNIT
			MIN.	TYP.	MAX.	
Input Load Current	I_{LI}	$V_{IN} = V_{IL}$ or V_{IH}	-10	-	10	µA
V_{CC} Program Current	I_{CP}	$\overline{CE} = V_{IL}$	-	-	30	mA
V_{PP} Program Current	I_{PP}	$\overline{CE} = V_{IL}$	-	-	30	mA
Input Low Voltage	V_{IL}	-	-0.3	-	0.8	V
Input High Voltage	V_{IH}	-	2.4	-	5.5	V
Output Low Voltage (Verify)	V_{OL}	I_{OL} = 2.1 mA	-	-	0.45	V
Output High Voltage (Verify)	V_{OH}	I_{OH} = -0.4 mA	2.4	-	-	V
A9 Silicon I.D. Voltage	V_{ID}	-	11.5	12.0	12.5	V
V_{PP} Program Voltage	V_{PP}	-	11.75	12.0	12.25	V
V_{CC} Supply Voltage (Program)	V_{CP}	-	4.5	5.0	5.5	V

AC PROGRAMMING/ERASE CHARACTERISTICS

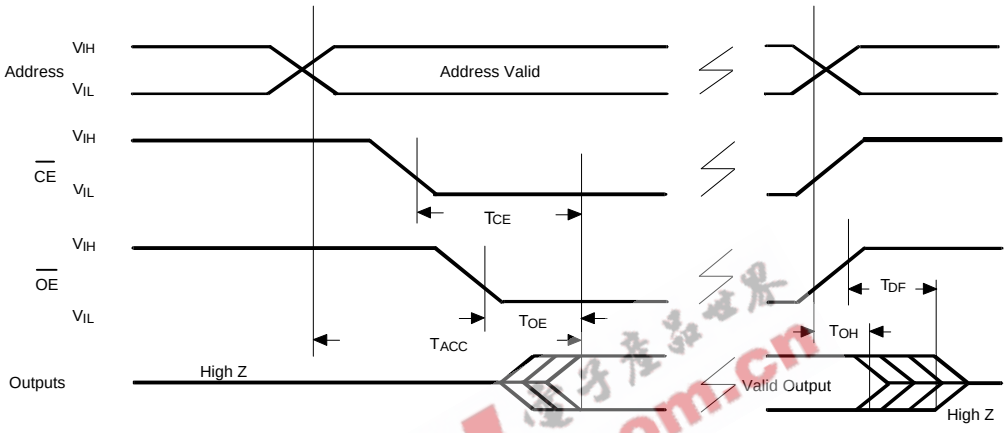
(V_{CC} = 5.0V ±10%, T_A = 25° C ±5° C)

PARAMETER	SYM.	LIMITS			UNIT
		MIN.	TYP.	MAX.	
V_{PP} Setup Time	T_{VPS}	2.0	-	-	µS
Address Setup Time	T_{AS}	2.0	-	-	µS
Data Setup Time	T_{DS}	2.0	-	-	µS
$\overline{CE}$ Program Pulse Width	T_{PWP}	95	100	105	µS
$\overline{CE}$ Erase Pulse Width	T_{PWE}	95	100	105	mS
Data Hold Time	T_{DH}	2.0	-	-	µS
$\overline{OE}$ Setup Time	T_{OES}	2.0	-	-	µS
Data Valid from $\overline{OE}$	T_{OEV}	-	-	150	nS
$\overline{OE}$ High to Output High Z	T_{DFP}	0	-	130	nS
Address Hold Time	T_{AH}	0	-	-	µS
Address Hold Time after $\overline{CE}$ High (Erase)	T_{AHC}	2.0	-	-	µS

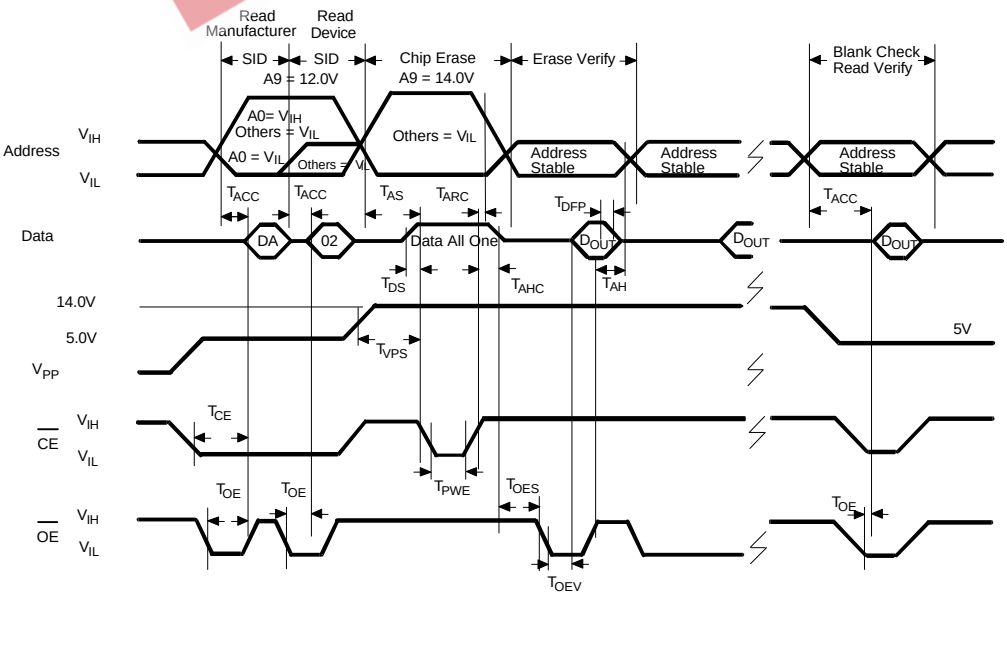
Note: V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.

TIMING WAVEFORMS

AC Read Waveform

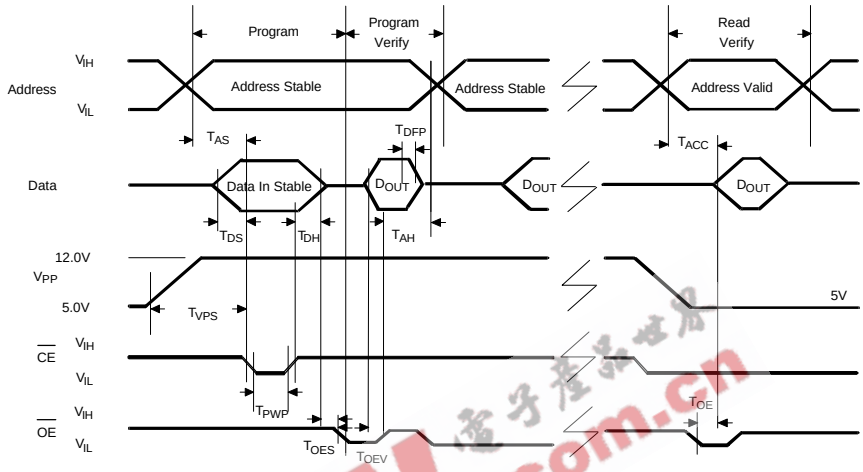


Erase Waveform

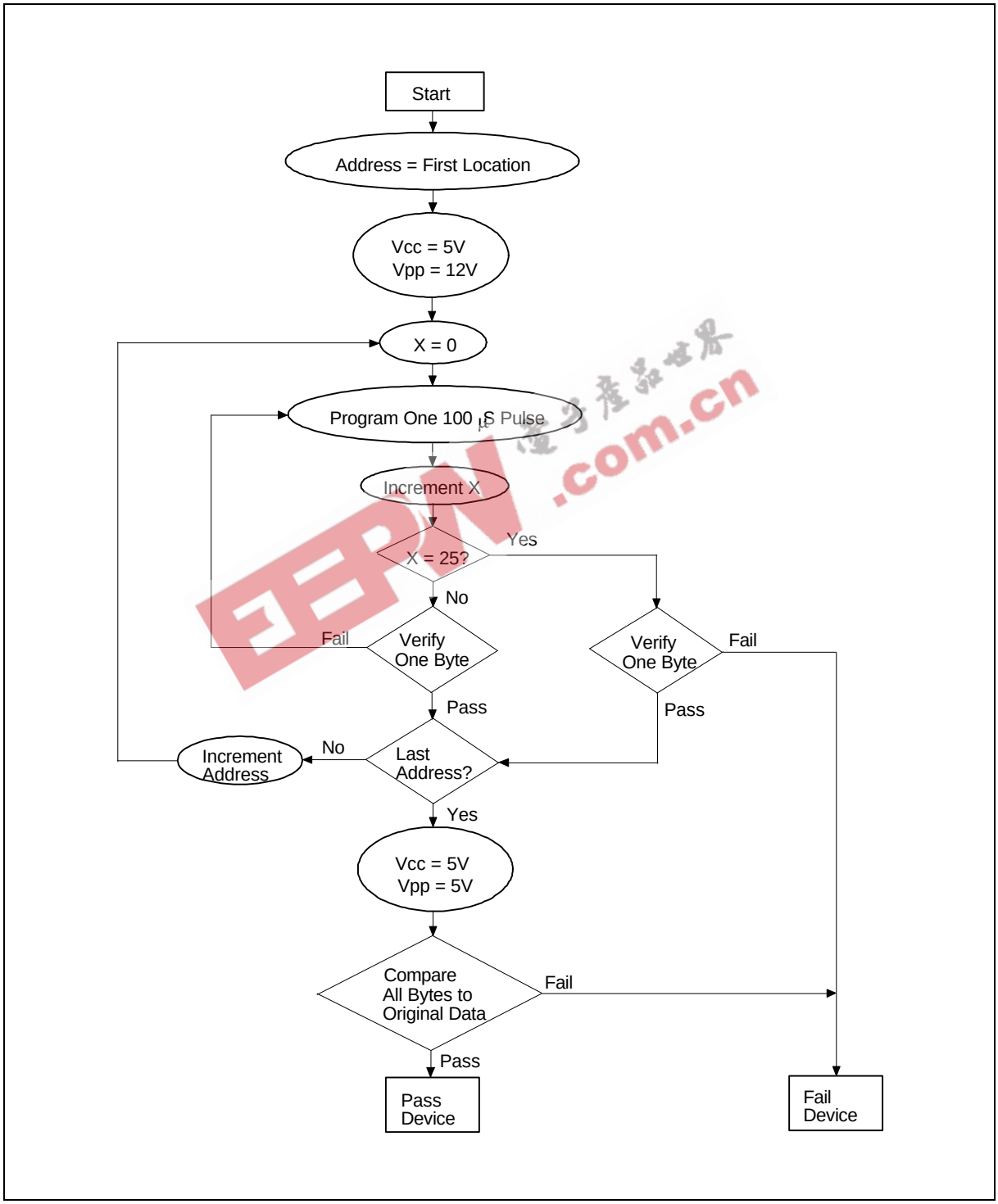


Timing Waveforms, continued

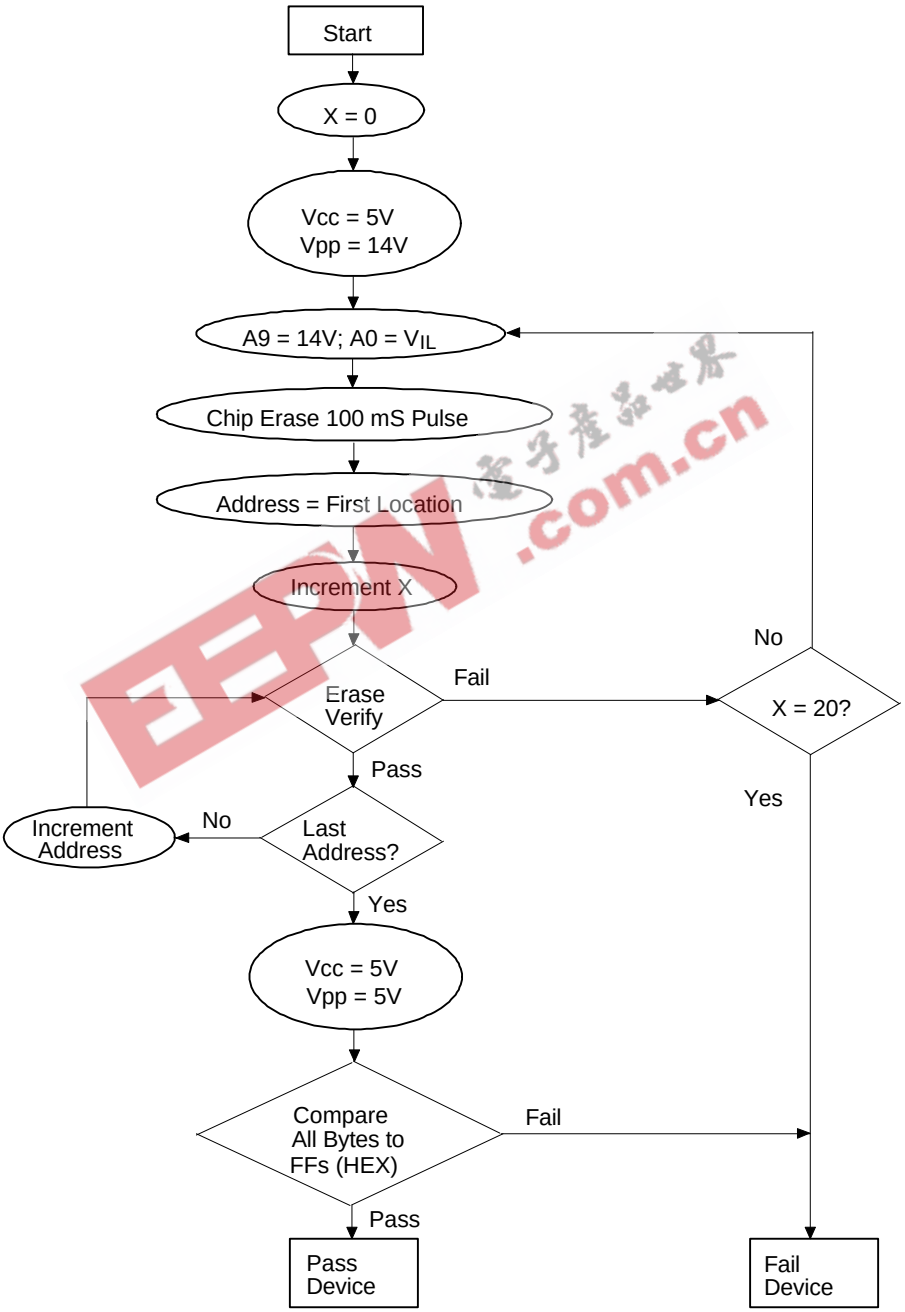
Programming Waveform



SMART PROGRAMMING ALGORITHM



SMART ERASE ALGORITHM



ORDERING INFORMATION

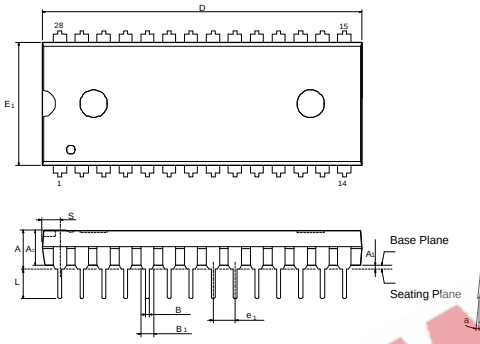
PART NO.	ACCESS TIME (nS)	POWER SUPPLY CURRENT MAX. (mA)	STANDBY Vcc CURRENT MAX. (μA)	PACKAGE
W27E257-10	100	30	100	600 mil DIP
W27E257-12	120	30	100	600 mil DIP
W27E257-15	150	30	100	600 mil DIP
W27E257P-10	100	30	100	32-pin PLCC
W27E257P-12	120	30	100	32-pin PLCC
W27E257P-15	150	30	100	32-pin PLCC

Notes:

1. Winbond reserves the right to make changes to its products without prior notice.
2. Purchasers are responsible for performing appropriate quality assurance testing on products intended for use in applications where personal injury might occur as a consequence of product failure.

PACKAGE DIMENSIONS

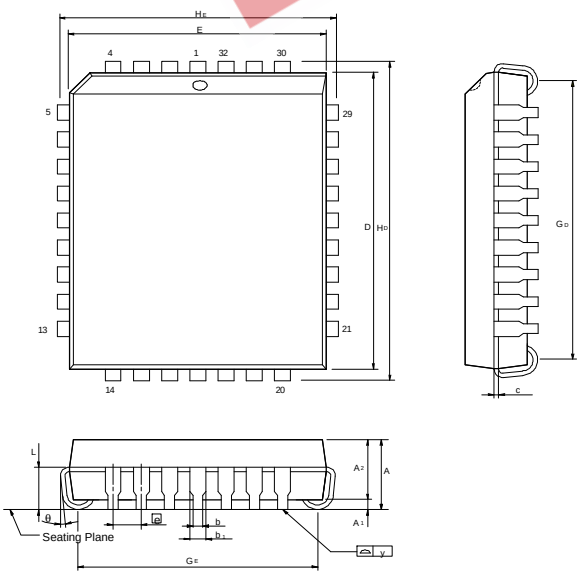
28-pin P-DIP



Symbol	Dimension in Inches			Dimension in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	—	—	0.210	—	—	5.33
A_1	0.010	—	—	0.25	—	—
A_2	0.150	0.155	0.160	3.81	3.94	4.06
B	0.016	0.018	0.022	0.41	0.46	0.56
B_1	0.058	0.060	0.064	1.47	1.52	1.63
c	0.008	0.010	0.014	0.20	0.25	0.36
D	—	1.460	1.470	—	37.08	37.34
E	0.590	0.600	0.610	14.99	15.24	15.49
E_1	0.540	0.545	0.550	13.72	13.84	13.97
e_1	0.090	0.100	0.110	2.29	2.54	2.79
L	0.120	0.130	0.140	3.05	3.30	3.56
a	0	—	15	0	—	15
e_A	0.630	0.650	0.670	16.00	16.51	17.02
S	—	—	0.090	—	—	2.29

Notes:
1. Dimension D Max. & S include mold flash or tie bar burrs.
2. Dimension E1 does not include interlead flash.
3. Dimension D & E1 include mold mismatch and are determined at the mold parting line.
4. Dimension B1 does not include dambar protrusion/intrusion.
5. Controlling dimension: Inches.
6. General appearance spec. should be based on final visual inspection spec.

32-pin PLCC



Symbol	Dimension in Inches			Dimension in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	—	—	0.140	—	—	3.56
A_1	0.020	—	—	0.50	—	—
A_2	0.105	0.110	0.115	2.67	2.80	2.93
b_1	0.026	0.028	0.032	0.66	0.71	0.81
b	0.016	0.018	0.022	0.41	0.46	0.56
c	0.008	0.010	0.014	0.20	0.25	0.35
D	0.547	0.550	0.553	13.89	13.97	14.05
E	0.447	0.450	0.453	11.35	11.43	11.51
e	0.044	0.050	0.056	1.12	1.27	1.42
G_D	0.490	0.51	0.530	12.45	12.9	13.46
G_E	0.390	0.410	0.430	9.91	10.41	10.92
H_D	0.585	0.590	0.595	14.86	14.99	15.11
H_E	0.485	0.49	0.495	12.32	12.45	12.57
L	0.075	0.090	0.095	1.91	2.29	2.41
y	—	—	0.004	—	—	0.10
θ	0°	—	10°	0°	—	10°

Notes:
1. Dimension D & E do not include interlead flash.
2. Dimension b does not include dambar protrusion/intrusion.
3. Controlling dimension: Inches.
4. General appearance spec. should be based on final visual inspection sepc.

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